

## **First Dual LDMOS Integrated Power Amplifiers Suited for Doherty Architecture and Compact Cellular Amplifier Designs**

At the IEEE MTT-S International Microwave Symposium, Infineon Technologies AG introduced an industry first series of dual integrated LDMOS power amplifier for wireless network base stations. Incorporating two LDMOS amplifiers in a single package, the devices provide two output power stages, making them well suited for Doherty-based amplifiers and for compact designs that benefit from reduced board space. Two of the new devices operate in the 1800 to 2200 MHz frequency range for WCDMA, LTE and TD-SCDMA applications, with output power of either 30W or 40W. The third device operates in the 700 to 1000 MHz for WCDMA, LTE and GSM/EDGE applications, with output power of 30 W. The dual amplifiers are particularly appropriate for Doherty-based designs, which employ separate main and peak power amplifiers to deliver the performance required for 3G and 4G systems. By enabling a reduced footprint for cellular base station amplifiers, the new dual LDMOS integrated amplifiers help address industry requirements for multi-carrier operation from a cell site. Multi-carrier and multi-band amplifier designs are also supported by wide RF modulation bandwidth. The PTMA080304M and PTMA21034M are available in 20-lead molded plastic packages and the PTMA21040FL is available in a thermally-enhanced open cavity package.

**Source URL (retrieved on 02/28/2015 - 1:35am):**

<http://www.wirelessdesignmag.com/news/2009/06/first-dual-ldmos-integrated-power-amplifiers-suited-doherty-architecture-and-compact-cellular-amplifier-designs?qt-blogs=0>